

L Number	Hits	Search Text	DB	Time stamp
1	0	(activat\$3 same (potential voltage)) and (electron near2 source) and (445/\$.ccls. (315/169.\$2).ccls. 345/\$.ccls.)	EPO; DERWENT	2003/09/30 09:38
2	310	(activat\$3 same (potential voltage)) and (electron near2 source) and (445/\$.ccls. (315/169.\$2).ccls. 345/\$.ccls.)	USPAT; US-PGPUB	2003/09/30 09:38
3	235	(activat\$3 same (potential voltage)) and (electron near2 source) and (445/\$.ccls. (315/169.\$2).ccls. 345/\$.ccls.) and ((electroconduct\$3 conduct\$3) near3 (film layer region portion section element))	USPAT; US-PGPUB	2003/09/30 09:39
4	201	(activat\$3 same (potential voltage)) and (electron near2 source) and (445/\$.ccls. (315/169.\$2).ccls. 345/\$.ccls.) and ((electroconduct\$3 conduct\$3) near3 (film layer region portion section element)) and (row column)	USPAT; US-PGPUB	2003/09/30 09:40
5	134	((activat\$3 same (potential voltage)) and (electron near2 source) and (445/\$.ccls. (315/169.\$2).ccls. 345/\$.ccls.) and ((electroconduct\$3 conduct\$3) near3 (film layer region portion section element)) and (row column)) not @ad>19991221	USPAT; US-PGPUB	2003/09/30 09:41
-	0	Tsuyoshi-takegami\$.in.	USPAT; US-PGPUB	2003/09/29 12:47
-	5	takegami-Tsuyoshi\$.in.	USPAT; US-PGPUB	2003/09/29 14:07
-	223	canon and ((applicat\$3 activat\$3) with voltage) and (electron near2 source) and (conduct\$3 near2 (section portion layer region film)) and (wiring line) and substrate	USPAT; US-PGPUB	2003/09/29 14:10
-	221	canon and ((applicat\$3 activat\$3) with voltage) and (electron near2 source) and (conduct\$3 near2 (section portion layer region film)) and (wiring line) and substrate and (method process)	USPAT; US-PGPUB	2003/09/29 14:11
-	100	canon and ((applicat\$3 activat\$3) with voltage) and (electron near2 source) and (conduct\$3 near2 (section portion layer region film)) and (wiring line) and substrate and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.)	USPAT; US-PGPUB	2003/09/29 14:11
-	89	canon and ((applicat\$3 activat\$3) with voltage) and (electron near2 source) and (conduct\$3 near2 (section portion layer region film)) and (wiring line) and substrate and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.) and row and column	USPAT; US-PGPUB	2003/09/29 14:17
-	165	((applicat\$3 activat\$3) with voltage) and (electron near2 source) and (conduct\$3 near2 (section portion layer region film)) and (wiring line) and substrate and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.) and row and column and (method process)	USPAT; US-PGPUB	2003/09/29 14:40
-	40	((applicat\$3 activat\$3) with voltage with (row column)) and (electron near2 source) and (conduct\$3 near2 (section portion layer region film)) and (wiring line) and substrate and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.) and (method process)	USPAT; US-PGPUB	2003/09/29 14:48
-	10	((applicat\$3 activat\$3) with voltage with (row column)) and (electron near2 source) and ((conduct\$3 near2 (section portion layer region film)) with (pair adjacent)) and (wiring line) and substrate and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.) and (method process)	USPAT; US-PGPUB	2003/09/29 14:49
-	9	((applicat\$3 activat\$3) with (potential voltage) with row) and (electron near2 source) and ((conduct\$3 near2 (section portion layer region film)) with (pair adjacent)) and (wiring line) and substrate and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.) and (method process)	USPAT; US-PGPUB	2003/09/29 14:51
-	9	((applicat\$3 activat\$3) with (potential voltage) with row) and (electron near2 source) and ((conduct\$3 near2 (section portion layer region film)) with (pair adjacent)) and (wiring line) and (445/\$.ccls. 324/\$.ccls. 345/\$.ccls.) and (method process)	USPAT; US-PGPUB	2003/09/29 15:07
-	1	((applicat\$3 activat\$3) with (potential voltage) with row) and (electron near2 source) and (((electroconduct\$3 conduct\$3) near2 (section portion layer region film)) with (pair adjacent)) and (wiring line) and (method process)	EPO; JPO; DERWENT	2003/09/29 15:08

-	35	((applicat\$3 activat\$3) with (potential voltage) with row) and (electron near2 source) and (((electroconduct\$3 conduct\$3) near2 (section portion layer region film)) with (pair adjacent)) and (wiring line) and (method process) 4849674.pn.	USPAT; US-PGPUB	2003/09/29 16:05
-	1		USPAT; US-PGPUB	2003/09/29 16:56
-	99	(445/24,25,49,50,51.ccls.) and (activat\$3 same (potential voltage)) and (electron near2 source) and ((electroconduct\$3 conduct\$3) near2 (region film layer section portion)) and (wire wiring line)	USPAT; US-PGPUB	2003/09/29 17:40
-	111	(445/.ccls.) and (activat\$3 same (potential voltage)) and (electron near2 source) and ((electroconduct\$3 conduct\$3) near2 (region film layer section portion)) and (wire wiring line) "09073859" "09134666"	USPAT; US-PGPUB	2003/09/29 17:56
-	4		EPO; JPO; DERWENT	2003/09/29 17:43
-	3	(activat\$3 same (potential voltage)) and (electron near2 source) and ((electroconduct\$3 conduct\$3) near2 (region film layer section portion)) and (wire wiring line)	EPO; DERWENT	2003/09/29 18:05
-	47	(activat\$3 same (potential voltage)) and (electron near2 source)	EPO; DERWENT	2003/09/30 09:37